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Sub	stitute for form 1449	PA/PTO		Сол	plete if Known
				Application Number	10/667,871
	INFORMATIO	N DISCLO	SURE	Filing Date	September 22, 2003
	STATEMENT	BY APPL	ICANT	First Named Inventor	Yeo, et al.
				Art Unit	2811
	(use as many sh	eets as nece	ssary)	Examiner Name	Unknown
Sheet	1	of	2	Attorney Docket Number	TSM03-0553

U.S. PATENT DOCUMENTS							
Examiner Initials*	Cite No.1	Document Number Number - Kind Code ^{2 (il known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
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Examiner Initials*	Cite ₁ No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	1 ²
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INFORMATION DISCLOSURE

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STATEMENT BY APPLICANT (use as many sheets as necessary)

of

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Complete if Known						
Application Number 10/667,871						
Filing Date	September 22, 2003					
First Named Inventor	Yeo, et al.					
Group Art Unit	2811					
Examiner Name	Unknown					
Attorney Docket Number	TSM03-0553					

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	
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20231* DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet of 3

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Complete if Known						
Application Number	10/667,871					
Filing Date	September 22, 2003					
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Examiner Name	TBD					
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Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	7
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				Application Number	10/667,871
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	TATEMENT I			First Named Inventor	Yeo, et al.
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				Examiner Name	TBD
Sheet	2	of	3	Attorney Docket Number	TSM03-0553

	т—	OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS		
Examiner	Cite	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the	Ţ.	
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				Application Number	10/667,871		
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		OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
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qu.	1	US- 2004/0026765 A1	02-12-2004	Currie, et al.		

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